

SLLS594B-MARCH 2004-REVISED OCTOBER 2004

LVDS 4x4 CROSSPOINT SWITCH

FEATURES

- Greater Than 2.0 Gbps Operation
- Nonblocking Architecture Allows Each Output to be Connected to Any Input
- Pk-Pk Jitter:
 - 60 ps Typical at 2.0 Gbps
 - 110 ps Typical at 2.5 Gbps
- Compatible With ANSI TIA/EIA-644-A LVDS
 Standard
- Available Packaging 38-Pin TSSOP
- 25 mV of Input Voltage Threshold Hysteresis
- Propagation Delay Times: 800 ps Typical
- Inputs Electrically Compatible With LVPECL, CML and LVDS Signal Levels
- Operates From a Single 3.3-V Supply
- Low Power: 110 mA Typical
- Integrated 110-Ω Line Termination Resistors Available With SN65LVDT250

APPLICATIONS

- Clock Buffering/Clock Muxing
- Wireless Base Stations
- High-Speed Network Routing
- Telecom/Datacom

DESCRIPTION

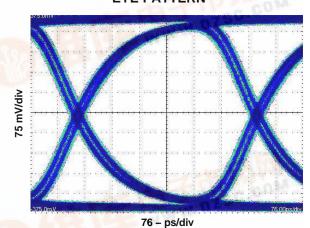
The SN65LVDS250 and SN65LVDT250 are 4x4 nonblocking crosspoint switches in a flow-through pin-out allowing for ease in PCB layout. Low-voltage differential signaling (LVDS) is used to achieve a high-speed data throughput while using low power. Each of the output drivers includes a 4:1 multiplexer to allow any input to be routed to any output. Internal signal paths are fully differential to achieve the high signaling speeds while maintaining low signal skews. The SN65LVDT250 incorporates $110-\Omega$ termination resistors for those applications where board space is a premium.

The SN65LVDS250 and SN65LVDT250 are characterized for operation from -40°C to 85°C.

SN65LVDS250DBT (Marked as LVDS250) SN65LVDT250DBT (Marked as LVDT250) (TOP VIEW)

S10 🗆	1 0	38	
S11 🗀	2	37	□ GND
1A 🗀	3	36	□□ 1Y
1B 🗀	4	35	□ 1Z
S20	5	34	1DE
S21	6	33	□□ 2Y
2A 🖵	7	32	2Z
2B 🖵	8	31	D 2DE
GND	9	30	GND GND
ACC	10	29	U VCC
GND	11 W-	28	□ GND
3A	12	27	□□ 3Y
3B	13	26	□□ 3Z
S30	14	25	□□ 3DE
S31	15	24	□□ 4Y
4A 🗀	16	23	□□ 4Z
4B 🞞	17	22	□□ 4DE
S40 🗀	18	21	☐ GND
S41 🗀	19	20	U vcc

EYE PATTERN



 V_{IC} = 1.2 V $|V_{ID}|$ = 200 mV 2 Gbps Input = PRBS 2²³ -1 V_{CC} = 3.3 V

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

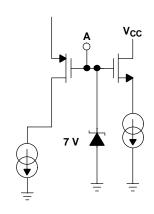
4DE 4Y

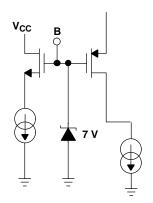
Integrated Termination on LVDT Only

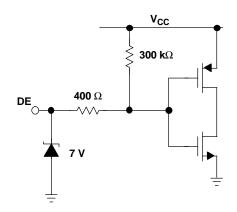


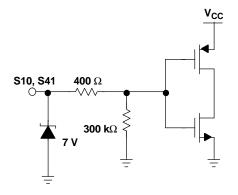
EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

INPUT LVDS250









OUTPUT LVDS250

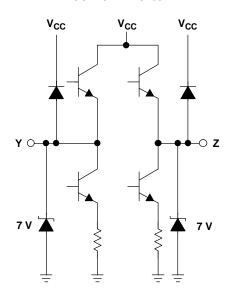




Table 1. CROSSPOINT LOGIC TABLES

OUTPUT CHANNEL 1			OUTPUT CHANNEL 2			OUTPUT CHANNEL 3			Ol	JTPUT C	HANNEL 4
	TROL NS	INPUT SELECTED		TROL NS	INPUT SELECTED	CONTROL PINS		INPUT SELECTED	CONTROL PINS		INPUT SELECTED
S10	S11	1Y/1Z	S20	S21	2Y/2Z	S30	S31	3Y/3Z	S40	S41	4Y/4Z
0	0	1A/1B	0	0	1A/1B	0	0	1A/1B	0	0	1A/1B
0	1	2A/2B	0	1	2A/2B	0	1	2A/2B	0	1	2A/2B
1	0	3A/3B	1	0	3A/3B	1	0	3A/3B	1	0	3A/3B
1	1	4A/4B	1	1	4A/4B	1	1	4A/4B	1	1	4A/4B

PACKAGE DISSIPATION RATINGS

PACKAGE	CIRCUIT BOARD MODEL	T _A ≤ 25°C POWER RATING	DERATING FACTOR ⁽¹⁾ ABOVE T _A = 25°C	T _A = 85°C POWER RATING
TSSOP (DBT)	Low-K ⁽²⁾	1038 mW	9.0 mW/°C	496 mW
TSSOP (DBT)	High-K ⁽³⁾	1772 mW	15.4 mW/°C	847 mW

- (1) This is the inverse of the junction-to-ambient thermal resistance when board-mounded and with no air flow.
- (2) In accordance with the Low-K thermal metric definitions of EIA/JESD51-6
- (3) In accordance with the High-K thermal metric definitions of EIA/JESD51-6

THERMAL CHARACTERISTICS

	PARAMETER	TEST CONDITIONS	VALUE	UNITS
Θ_{JB}	Junction-to-board thermal resistance		40.3	°C/W
$\Theta_{\sf JC}$	Junction-to-case thermal resistance		8.5	C/VV
D	Device power discipation	V _{CC} = 3.3 V, T _A = 25°C, 1 GHz	356	mW
P_D	Device power dissipation	V _{CC} = 3.6 V, T _A = 85°C, 1 GHz	522	mW

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted (1)

			UNITS	
Supply voltage range, V _{CC}			-0.5 V to 4 V	
	S, DE		-0.5 V to 4 V	
Valtaga ranga(2)	А, В	A, B		
Voltage range ⁽²⁾	V _A - V _B (LVDT only)	V _A - V _B (LVDT only)		
	Y, Z	Y, Z		
	Human body model ⁽³⁾	All pins	±3 kV	
Electrostatic discharge	Charged-device model ⁽⁴⁾	All pins	±500 V	
Continuous power dissipation	1		See Dissipation Rating Table	

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
- (3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (4) Tested in accordance with JEDEC Standard 22, Test Method C101.



RECOMMENDED OPERATING CONDITIONS

			MIN	NOM MA	X UNIT
V _{CC}	Supply voltage		3	3.3 3	6 V
V _{IH}	High-level input voltage	S10-S41, 1DE-4DE	2	V	c V
V _{IL}	Low-level input voltage	S10-S41, 1DE-4DE	0	0	8 V
157 1	Manaituda of differential insultural	LVDS	0.1		1 V
$ V_{ID} $	Magnitude of differential input voltage	LVDT	0.1	0	8 V
	Input voltage (any combination of common	-mode or input signals)	0	3	3 V
TJ	Junction temperature			14	0 °C
T _A (1)	Operating free-air temperature		-40	}	5 °C

⁽¹⁾ Maximum free-air temperature operation is allowed as long as the device maximum junction temperature is not exceeded.

TIMING SPECIFICATIONS

	PARAMETER			NOM	MAX	UNIT
t _{SET}	Input to select setup time			0.6		ns
t _{HOLD}	Input to select hold time	See Figure 7		0.2		ns
t _{SWITCH}	Select to switch output			1.2	1.6	ns

INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted (1)

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IT+}	Positive-going differential input voltage	threshold	See Figure 1			100	mV
V _{IT-}	Negative-going differential input voltage	e threshold	See Figure 1	-100			mV
V _{ID(HYS)}	Differential input voltage hysteresis				25		mV
	High lovel input current	1DE-4DE	V 2V	-10			
I _{IH}	High-level input current	S10-S41	V _{IH} = 2 V			20	μΑ
	Lavi lavalianut aumant	1DE-4DE	.,				
'IL	I _{IL} Low-level input current S10-S41		Low-level input current S10-S41 V _{IL} = 0.8 V			20	μΑ
I _I	Input current (A or B inputs)		V _I = 0 V or 3.3 V, second input at 1.2 V (other input open for LVDT)	-20		20	μΑ
I _{I(OFF)}	Input current (A or B inputs)		$V_{CC} \le 1.5 \text{ V}, V_I = 0 \text{ V or } 3.3 \text{ V, second}$ input at 1.2 V(other input open for LVDT)	-20		20	μΑ
I _{IO}	Input offset current (I _{IA} - I _{IB}) (LVDS)		$V_{IA} = V_{IB, 0} \le V_{IA} \le 3.3 \text{ V}$	-6		6	μA
	Termination resistance (LVDT)		V_{ID} = 300 mV, V_{IC} = 0 V to 3.3 V	90	110	132	
R _T Termination resistance (LVDT with power-off)		$V_{ID} = 300 \text{ mV}, V_{IC} = 0 \text{ V to } 3.3 \text{ V}, V_{CC} = 1.5 \text{ V}$	90	110	132	Ω	
C _I	Differential input capacitance				2.5		pF

⁽¹⁾ All typical values are at 25° C and with a 3.3 V supply.

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OUTPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OD}	Differential output voltage magnitude	See Figure 2	247	350	454	mV
$\Delta V_{OD} $	Change in differential output voltage magnitude between logic states	$V_{ID} = \pm 100 \text{ mV}$	-50		50	mV
V _{OC(SS)}	Steady-state common-mode output voltage		1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50		50	mV
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage			50	150	mV
I _{CC}	Supply current	R _L =100 Ω		110	145	mA
Ios	Short-circuit output current	V_{OY} or $V_{OZ} = 0 V$	-27		27	mA
I _{OSD}	Differential short circuit output current	$V_{OD} = 0 V$	-12		12	mA
l _{OZ}	High-impedance output current	$V_O = 0 \text{ V or } V_{CC}$			±1	μΑ
Co	Differential output capacitance			2		pF

SWITCHING CHARACTERISTICS

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output		700	800	1200	
t _{PHL}	Propagation delay time, high-to-low-level output	See Figure 4	700	800	1200	20
t _r	Differential output signal rise time (20%-80%)	See Figure 4		200	245	ps
t _f	Differential output signal fall time (20%-80%)			200	245	
t _{sk(p)}	Pulse skew (t _{PHL} - t _{PLH}) ⁽¹⁾			0	50	ps
t _{sk(o)}	Channel-to-channel output skew ⁽²⁾				175	ps
t _{sk(pp)}	Part-to-part skew ⁽³⁾				300	ps
t _{jit(per)}	Period jitter, rms (1 standard deviation) ⁽⁴⁾	See Figure 6		1	3	ps
t _{jit(cc)}	Cycle-to-cycle jitter (peak) ⁽⁵⁾	See Figure 6		8	17	ps
t _{jit(pp)}	Peak-to-peak jitteR (6)	See Figure 6		60	110	ps
t _{jit(det)}	Deterministic jitter, peak-to-peak ⁽⁷⁾	See Figure 6		48	65	ps
t _{PHZ}	Propagation delay, high-level-to-high-impedance output				6	
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	Coo Figuro F			6	
t _{PZH}	Propagation delay, high-impedance -to-high-level output	See Figure 5			300	ns
t _{PZL}	Propagation delay, high-impedance-to-low-level output				300	

- $t_{\text{sk(p)}}$ is the magnitude of the time difference between the t_{PLH} and t_{PHL} of any output of a single device.
- $t_{sk(0)}$ is the maximum delay time difference between drivers over temperature, V_{CC} , and process.
- $t_{sk(p)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. Input voltage = V_{ID} = 200 mV, 50% duty cycle at 1.0 GHz, t_r = t_f = 50 ps (20% to 80%), measured over 1000 samples. Input voltage = V_{ID} = 200 mV, 50% duty cycle at 1.0 GHz, t_r = t_f = 50 ps (20% to 80%). Input voltage = V_{ID} = 200 mV, 2²³-1 PRBS pattern at 2.0 Gbps, t_r = t_f = 50 ps (20% to 80%). Input voltage = V_{ID} = 200 mV, 2⁷-1 PRBS pattern at 2.0 Gbps, t_r = t_f = 50 ps (20% to 80%).
- (5)



PARAMETER MEASUREMENT INFORMATION

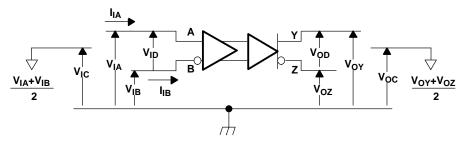


Figure 1. Voltage and Current Definitions

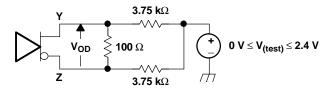
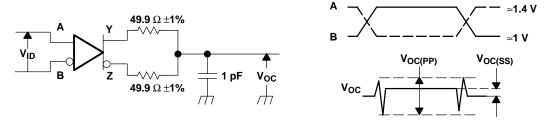
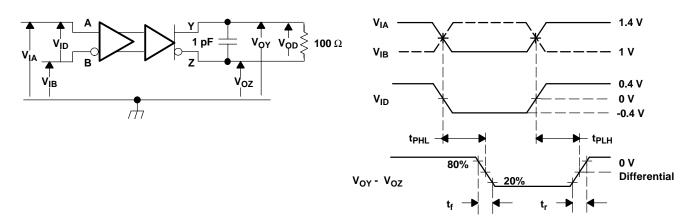


Figure 2. Differential Output Voltage (VoD) Test Circuit



A. All input pulses are supplied by a generator having the following characteristics: t_r or t_f≤ 1 ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ±10 ns; R_L = 100Ω; C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT; the measurement of V_{OC(PP)} is made on test equipment with a -3 dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions fot the Driver Common-Mode Output Voltage

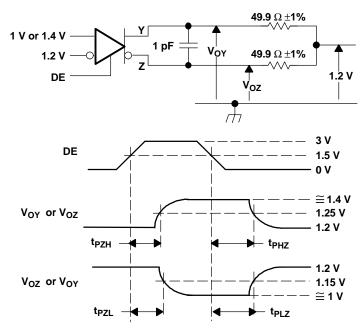


A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \le 0.25$ ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns . C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

Figure 4. Timing Test Circuit and Waveforms

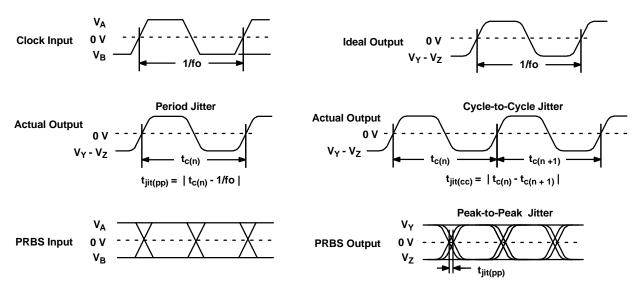


PARAMETER MEASUREMENT INFORMATION (continued)



A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_r \le 1$ ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns. C_L includes instrumentation and fixture capacitance within 0,06 mm of the DUT.

Figure 5. Enable and Disable Time Circuit and Definitions

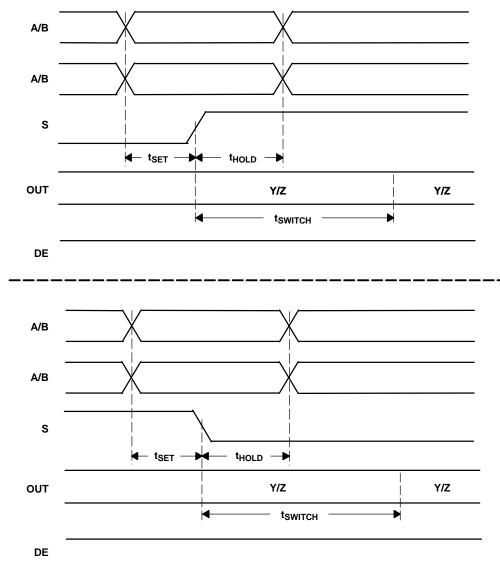


- A. All input pulses are supplied by an Agilent 81250 Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software.

Figure 6. Driver Jitter Measurement Waveforms



PARAMETER MEASUREMENT INFORMATION (continued)



A. t_{SET} and t_{HOLD} times specify that data must be in a stable state before and after mux control switches.

Figure 7. Input to Select for Both Rising and Falling Edge Setup and Hold Times



TYPICAL CHARACTERISTICS

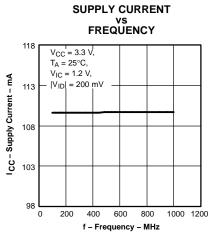


Figure 8.

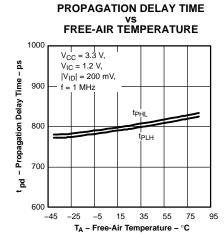
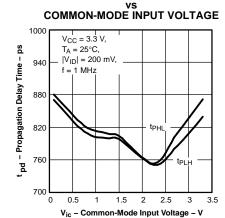


Figure 9.

PEAK-TO-PEAK JITTER



PROPAGATION DELAY TIME

Figure 10.

PEAK-TO-PEAK JITTER

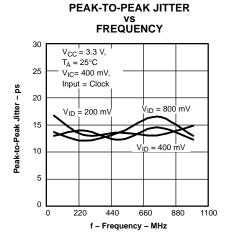


Figure 11.

PEAK-TO-PEAK JITTER

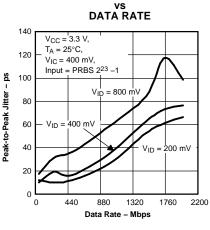


Figure 12.

PEAK-TO-PEAK JITTER

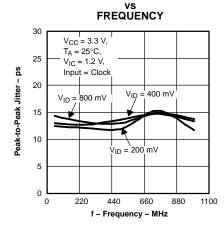


Figure 13.

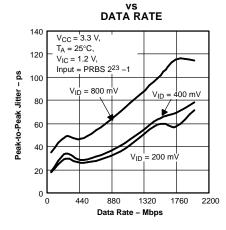


Figure 14.

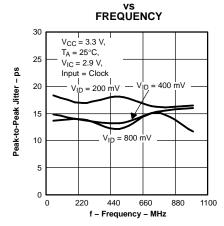


Figure 15.

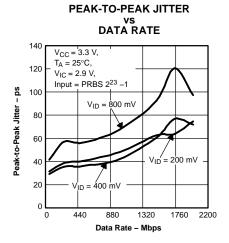


Figure 16.



TYPICAL CHARACTERISTICS (continued)

PEAK-TO-PEAK JITTER vs FREE-AIR TEMPERATURE

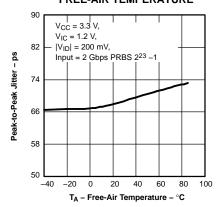


Figure 17.

DIFFERENTIAL OUTPUT VOLTAGE vs FREQUENCY

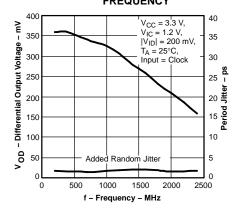


Figure 19.

PEAK-TO-PEAK JITTER VS DATA RATE

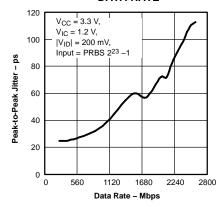
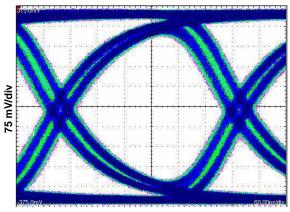


Figure 18.

EYE PATTERN



60 - ps/div

 V_{IC} = 1.2 V, $|V_{ID}|$ = 200 mV, 2.5 Gbps, Input = PRBS 2²³ –1, V_{CC} = 3.3 V

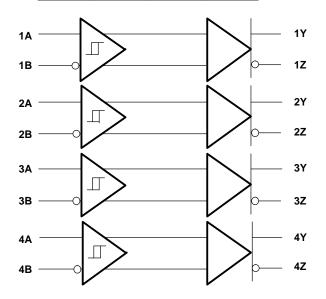
Figure 20.



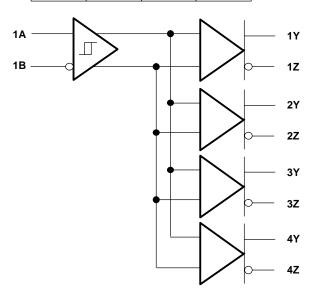
APPLICATION INFORMATION

CONFIGURATION EXAMPLES

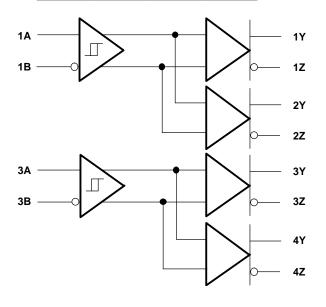
S10	S11	S20	S21
0	0	0	1
S30	S31	S40	S41
1	0	1	1



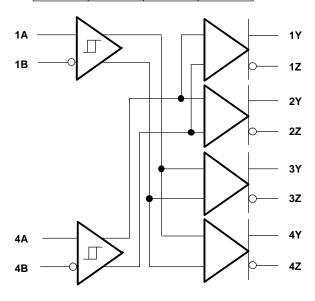
S10	S11	S20	S21
0	0	0	0
S30	S31	S40	S41
0	0	0	0



	S10	S11	S20	S21
	0	0	0	0
	S30	S31	S40	S41
ı	1	0	1	0



S10	S11	S20	S21
1	1	1	1
S30	S31	S40	S41
0	0	0	0





APPLICATION INFORMATION (continued)

TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, etc.)

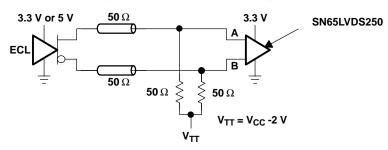


Figure 21. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)

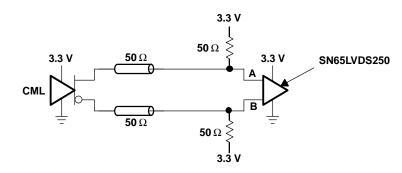


Figure 22. Current-Mode Logic (CML)

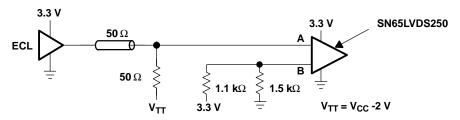


Figure 23. Single-Ended (LVPECL)

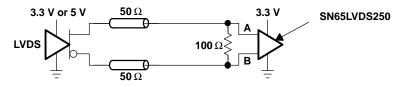


Figure 24. Low-Voltage Differential Signaling (LVDS)



PACKAGE OPTION ADDENDUM

8-Aug-2005

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65LVDS250DBT	ACTIVE	SM8	DBT	38	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LVDS250DBTR	ACTIVE	SM8	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LVDS250DBTRG4	ACTIVE	SM8	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LVDT250DBT	ACTIVE	SM8	DBT	38	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LVDT250DBTR	ACTIVE	SM8	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
SN65LVDT250DBTRG4	ACTIVE	SM8	DBT	38	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

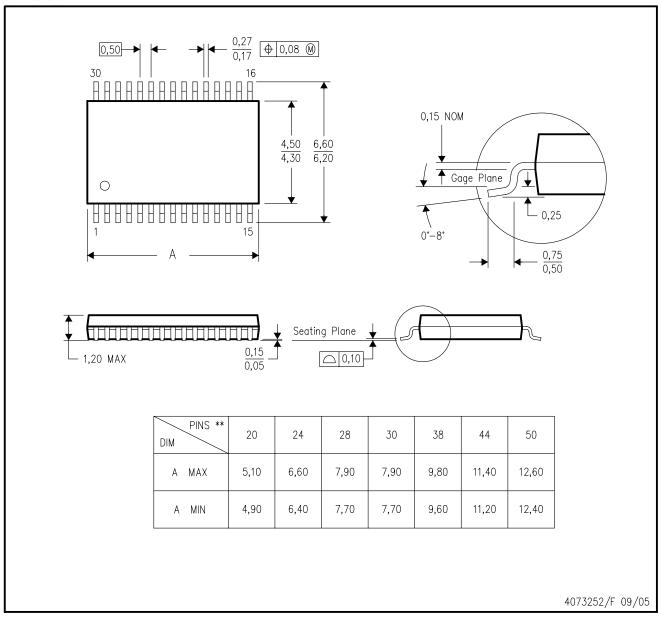
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DBT (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

30 PINS SHOWN



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-153 except 44 pin package length.



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